

Online Radiation Dose Measurement System for ATLAS experiment

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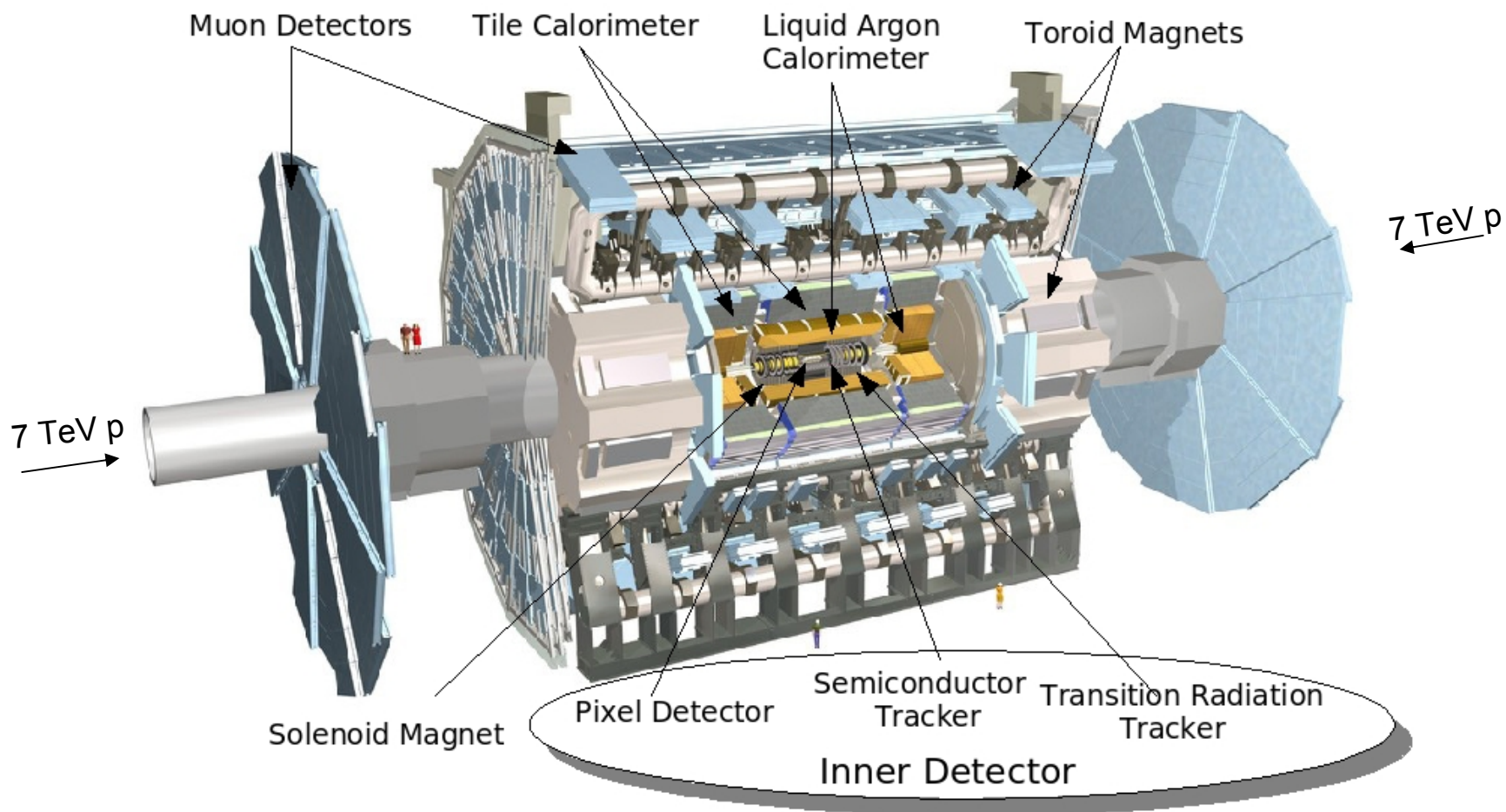
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Lot of work with radiation sensors (characterization, selection, calibration, annealing studies etc...) was done by F. Ravotti, M. Glaser, M. Moll et al. from the CERN RADMON team
<http://lhc-expt-radmon.web.cern.ch/lhc-expt-radmon/>

The ATLAS experiment

- experiment at the Large Hadron Collider at CERN
- proton-proton collisions, $E_p = 7 \text{ TeV}$, Luminosity = $10^{34} \text{ cm}^{-2}\text{s}^{-1}$

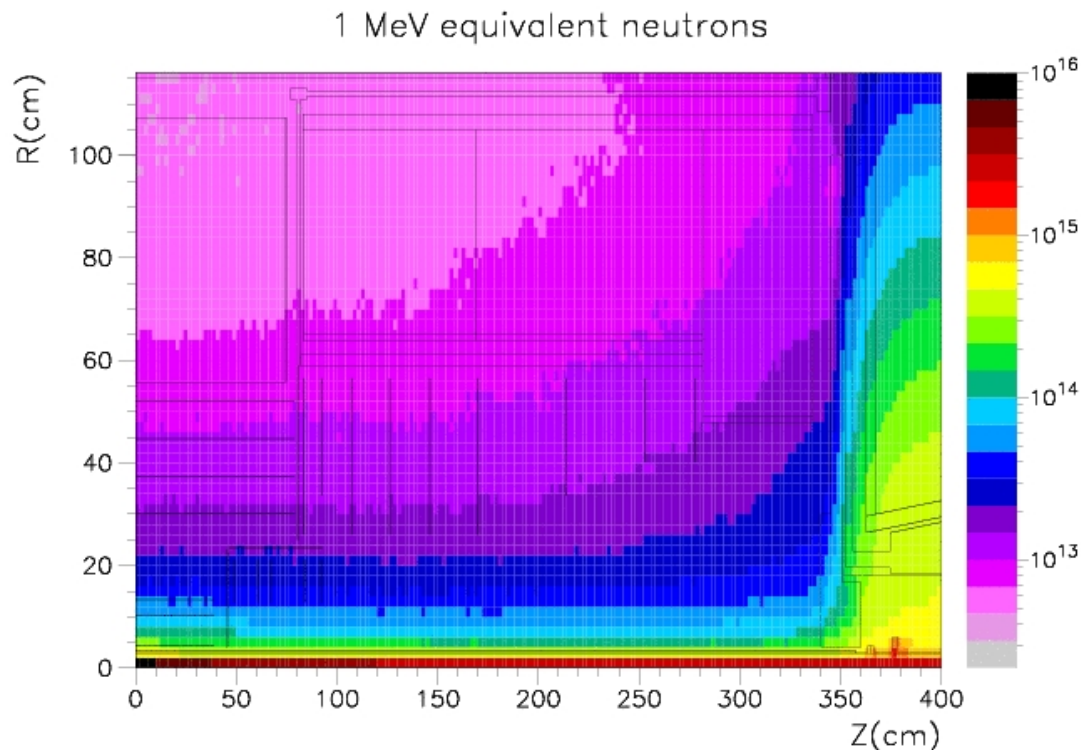


Radiation Field in ATLAS

- secondary particles from p-p interaction point - mostly pions
- radiation from interaction of secondary particles with detector material - neutrons

Radiation levels after 10 years of LHC operation:

- Total Ionizing Dose (TID):
TID > 100 kGy
- Non Ionizing Energy Loss (NIEL):
 $\Phi_{\text{eq}} \sim 10^{15} \text{ n/cm}^2$
(1 MeV equivalent neutrons in Si)
- Thermal neutrons $\Phi \sim 10^{15} \text{ n/cm}^2$

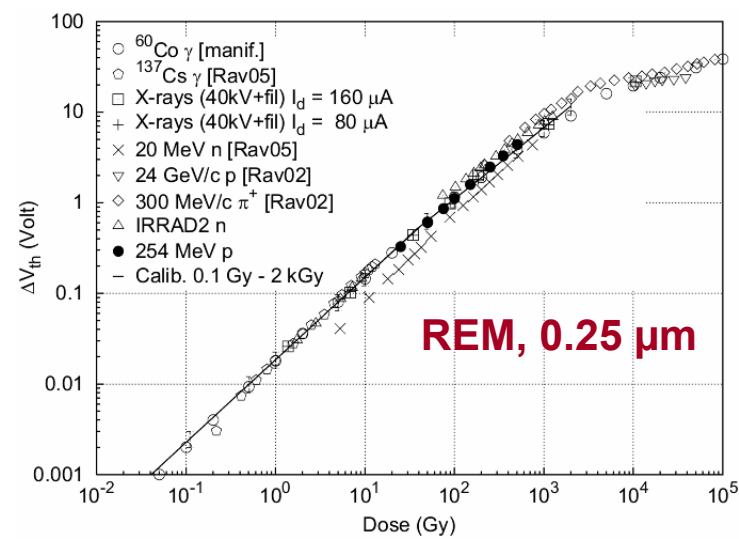
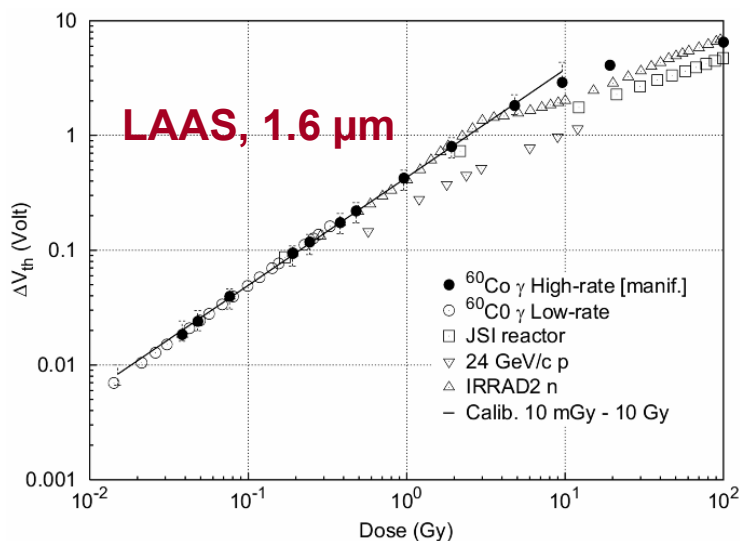
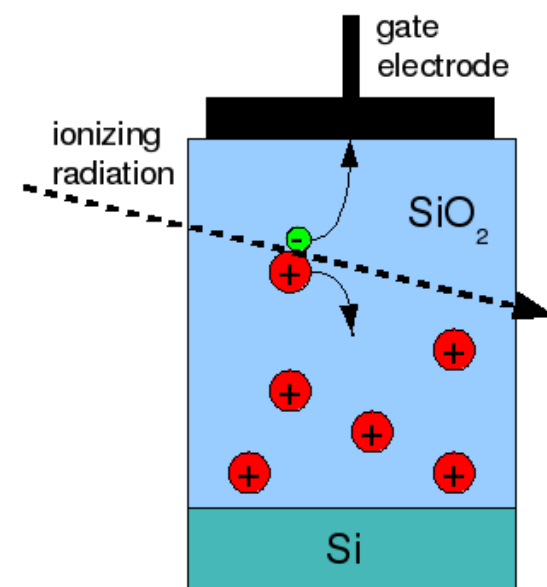


- such radiation levels cause damage to detectors and readout electronics
 - ➔ dose monitoring necessary to understand detector performance
 - ➔ cross check of simulations and make predictions

TID measurements with RadFETs

- RadFETs: p-MOS transistor
- holes created by radiation get trapped in the gate oxide:
 - ➔ increase of threshold voltage with dose:

$$\Delta V = a \times (TID)^b$$
- sensitivity and dynamic range depends on oxide thickness:



- characterizations, selection, calibrations done by CERN RADMON team:
F. Ravotti, M. Glaser, M. Moll....

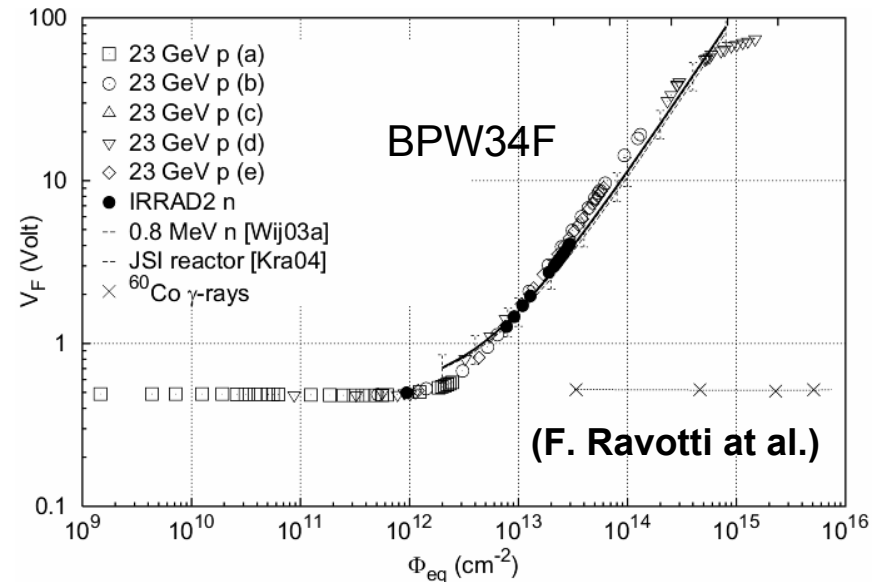
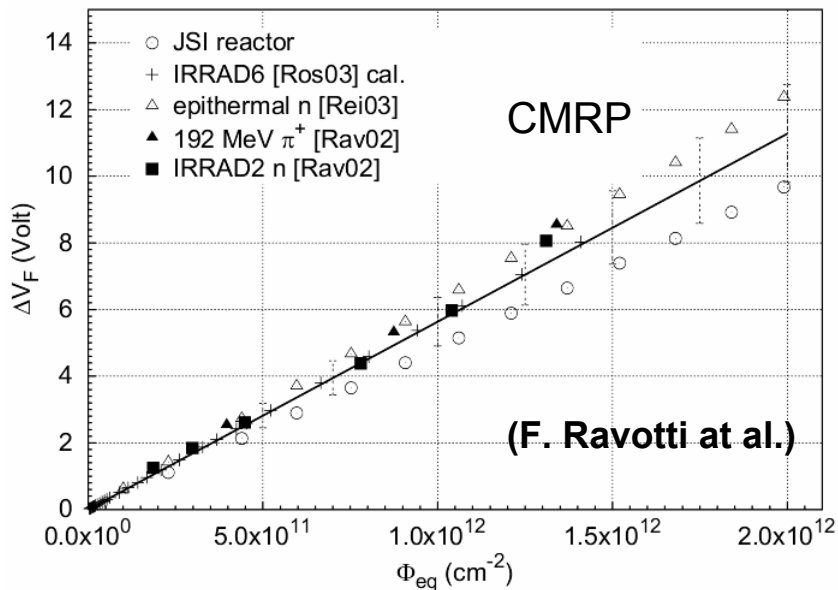
NIEL measurements with diodes

- bulk damage in silicon consequence:
increased resistance, increase of reverse current....

- ➔ forward bias: forward voltage at given forward current increases
- ➔ reverse bias: reverse current increases

Forward bias

- linear response $\Delta V = k \cdot \Phi_{eq}$ (V measured at $I = 1 \text{ mA}$)
- high sensitivity diode (CMRP, University of Wollongong, AU) 10^9 to $\sim 10^{12} \text{ n/cm}^2$,
- commercial (Osram) silicon PIN photodiode BPW34F 10^{12} to $\sim 10^{15} \text{ n/cm}^2$



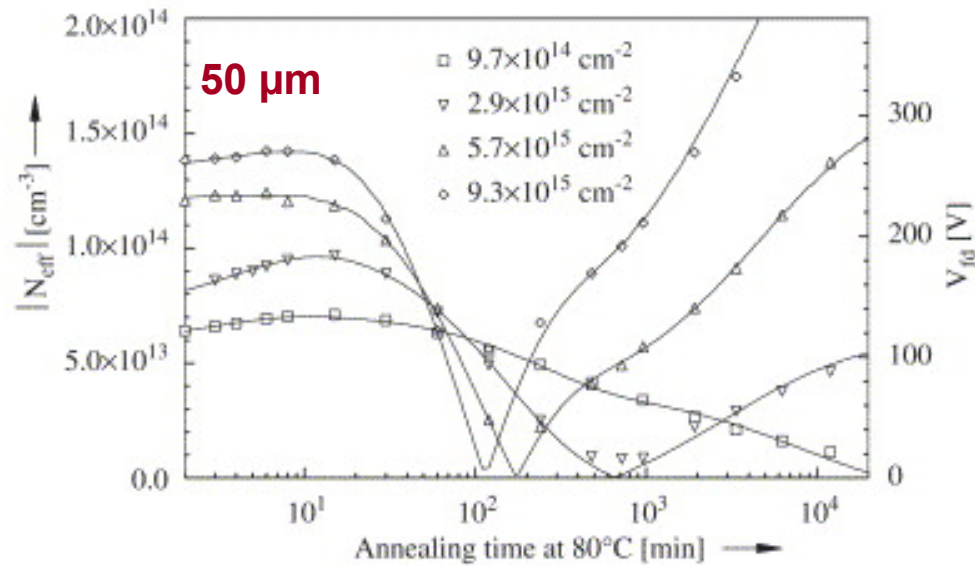
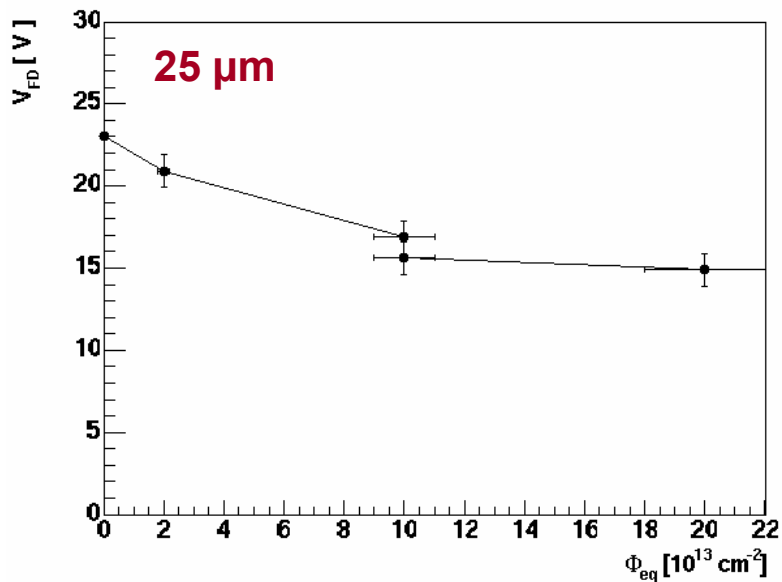
➔ sensitivity can be shifted to lower Φ if diode is pre-irradiated with $\sim 3 \cdot 10^{12} \text{ n/cm}^2$

NIEL measurements with diodes

Reverse bias

Reverse current proportional to fluence $I = \Phi_{eq}/\alpha V$

- **25 μm** x 0.5 cm x 0.5 cm pad diode with guard ring structure processed on **epitaxial silicon**
 - **thin epitaxial** diode can be depleted with $V_{\text{bias}} < 30$ V also after irradiation with 10^{15} n/cm²
 - in this fluence and time range V_{bias} does not increase with annealing
- suitable to measure fluences from 10^{11} n/cm² to 10^{15} n/cm²



G. Lindström et al., NIMA 568 (2006)

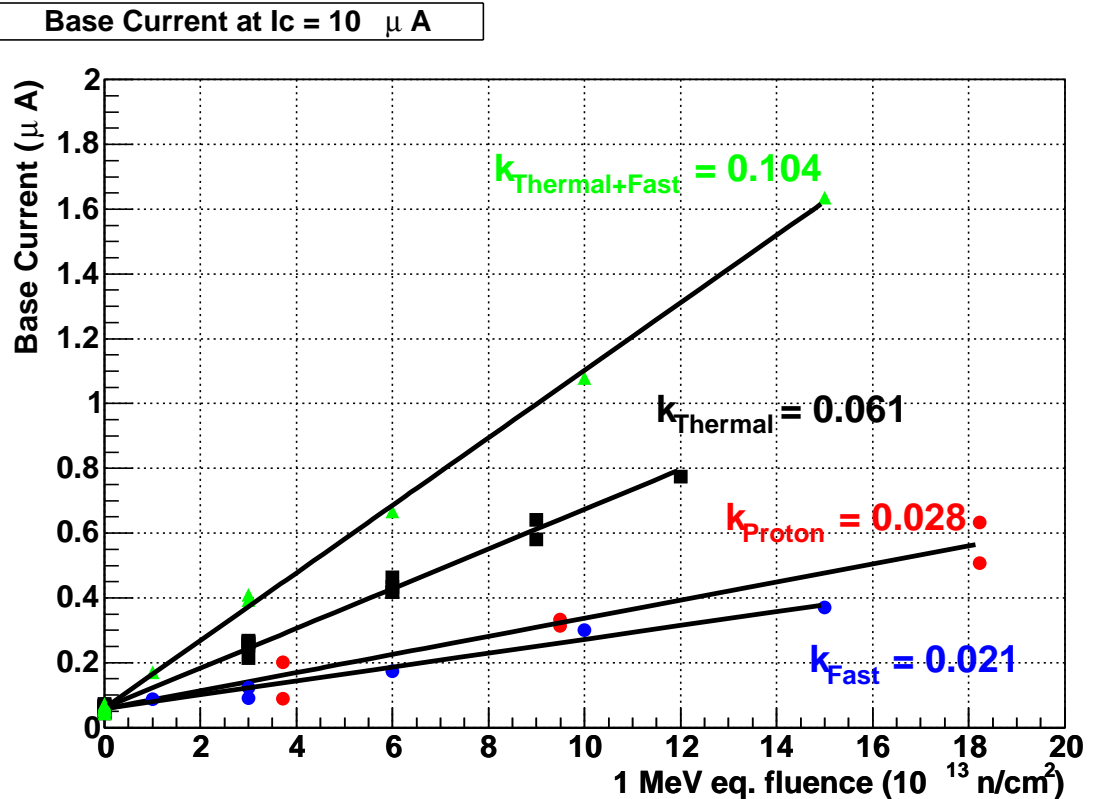
Thermal neutrons

- bipolar transistors (DMILL) used in front end ASICs
 - measure current gain: base current at given collector current
- sensitive to fast and thermal neutrons

$$\Delta I_b / I_c = k_{eq} \cdot \Phi_{eq} + k_{th} \cdot \Phi_{th}$$

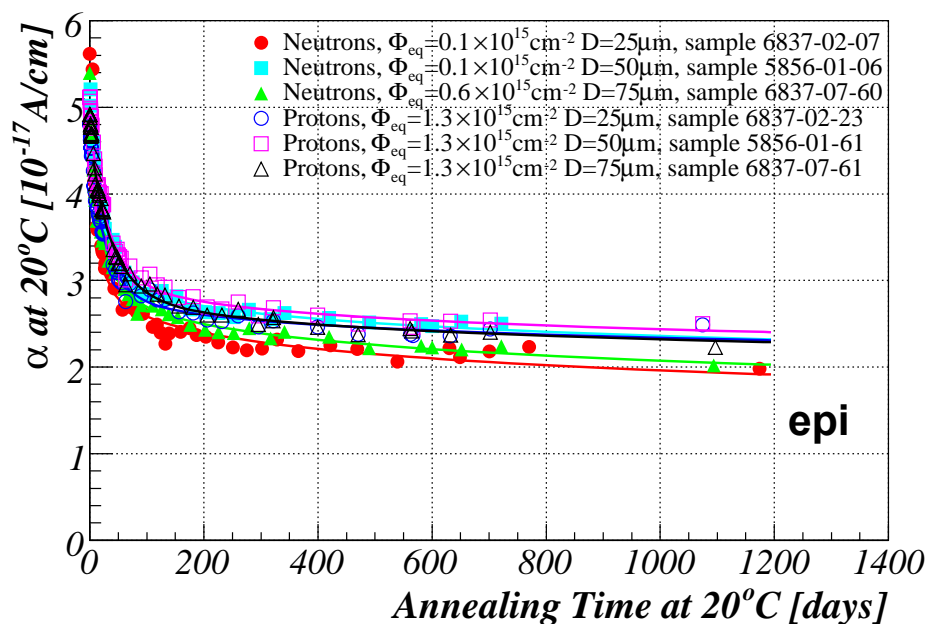
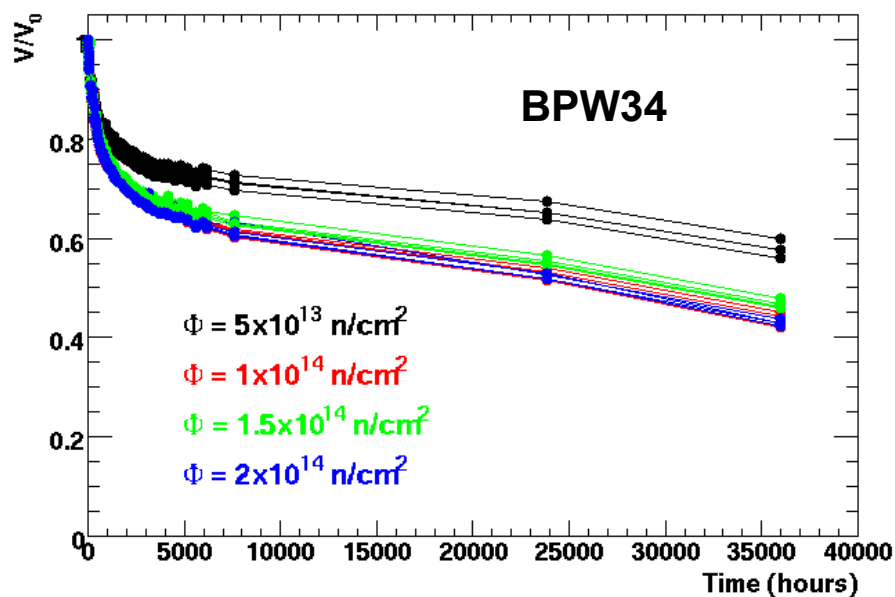
k_{eq} , k_{th} and Φ_{eq} known

→ Φ_{th} can be determined



Annealing

- not significant ($\sim 15\%$ or less in 1 year at RT): RadFETs, DMILL transistors, CMRP diodes
- larger: BPW34, epi



Radiation Monitor Sensor Board (RMSB)

Inner Detector

- for dose monitoring in the Inner Detector:

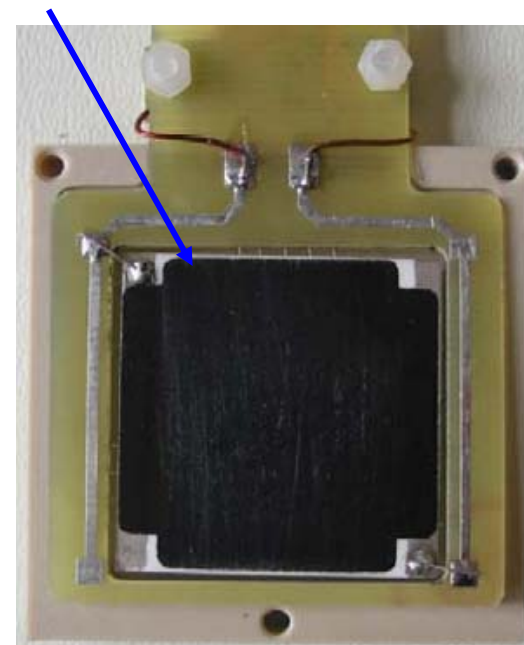
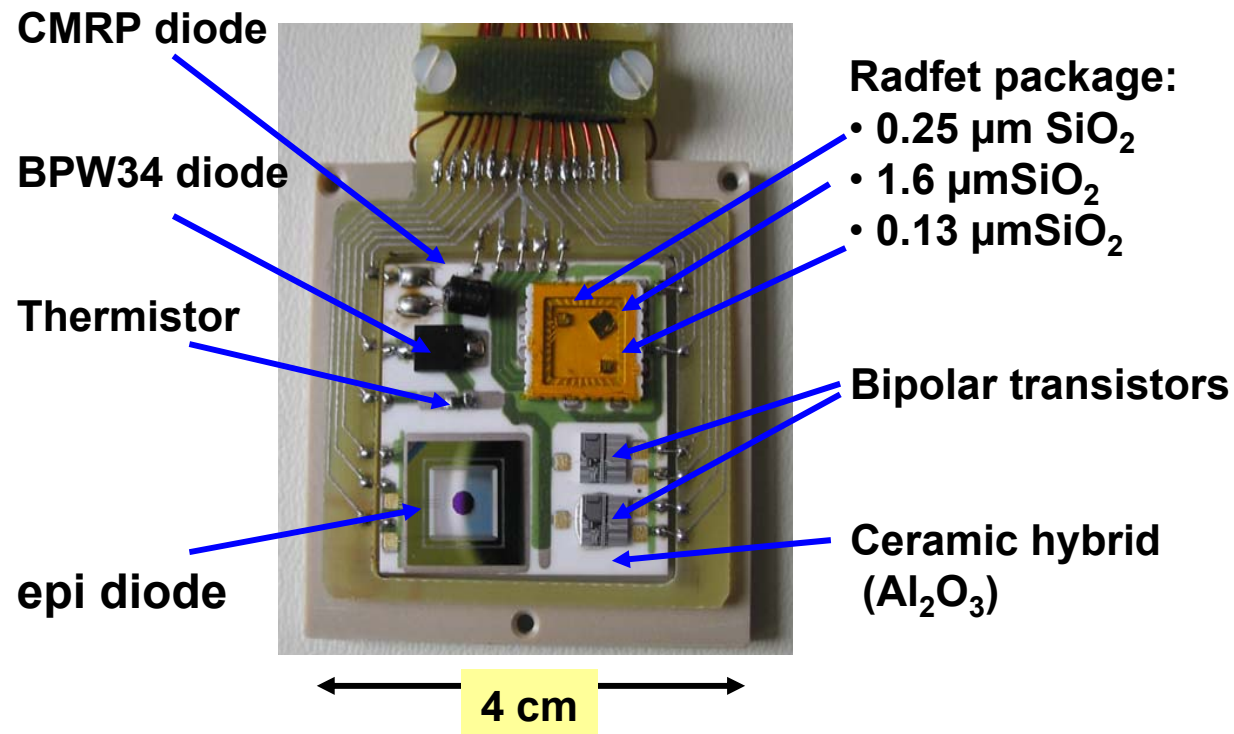
- large range of doses
- no access in 10 years

→ **need many sensors**

- large temperature variations (-10 to 20°C) at some locations

→ stabilize temperature to $20 \pm 1^\circ\text{C}$ by heating back side of the ceramic hybrid

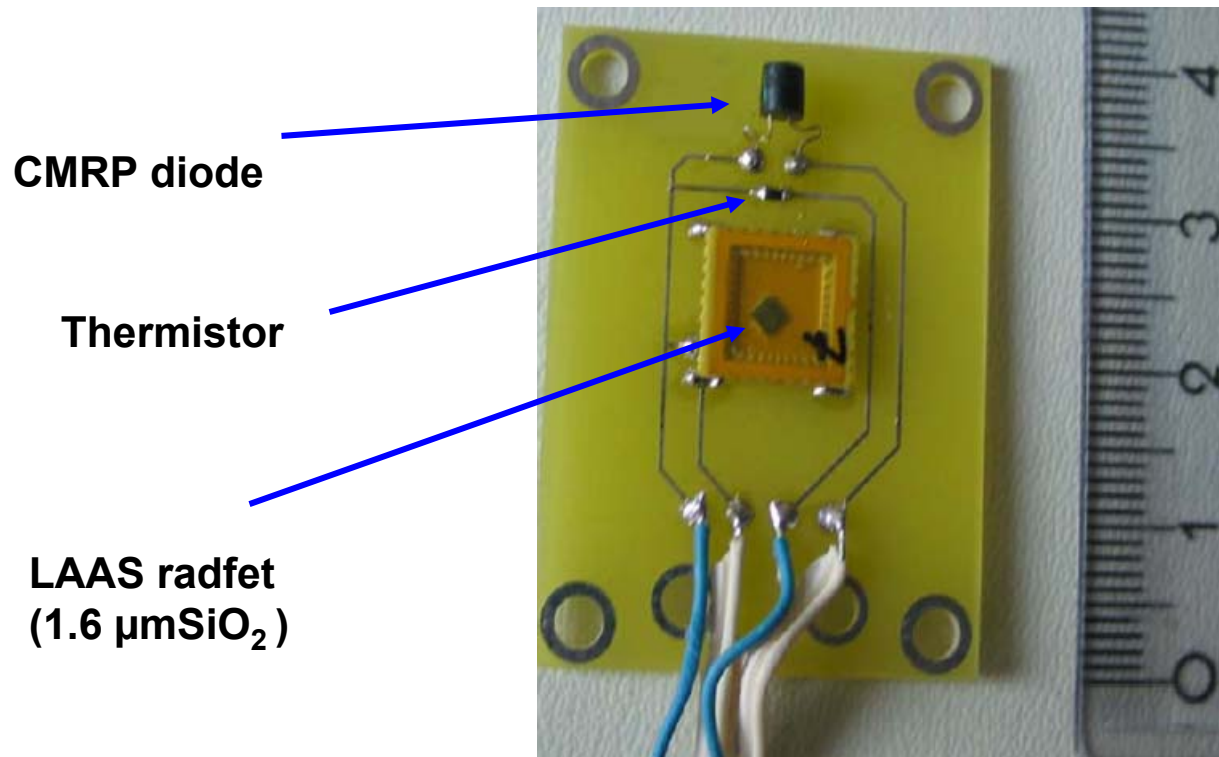
Thick film resistive layer $R = 320 \Omega$



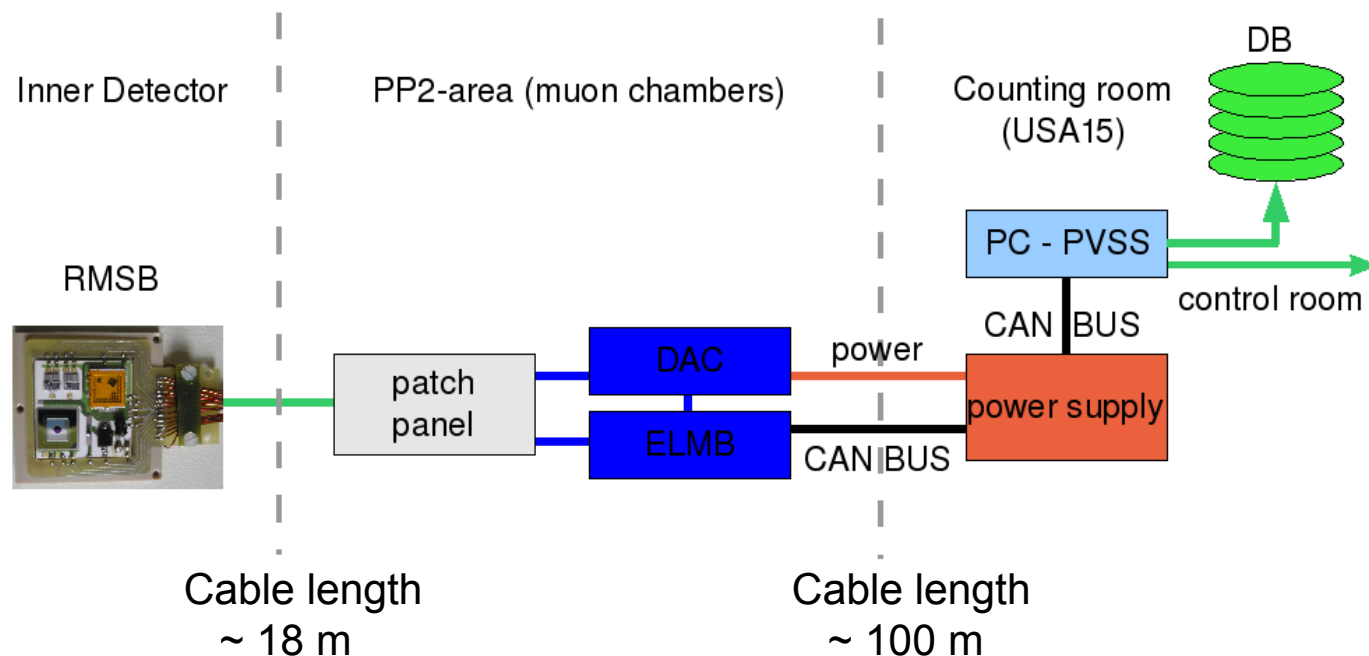
Radiation Monitor Sensor Board (RMSB)

Other locations

- lower dose ranges
→ mGy to 10 Gy, 10^9 to $\sim 10^{12}$ n/cm²
- no temperature stabilization
→ correct read out values with known temperature dependences



- use standard ATLAS Detector Control System components
 - **ELMB:**
 - 64 ADC channels
 - can bus communication
 - **ELMB-DAC:**
 - current source, 16 channels ($I_{\max} = 20 \text{ mA}$, $U_{\max} = 30 \text{ V}$)
- sensors are biased only during readout (\sim few minutes every hour)
- software written in PVSS
- readout values available in the ATLAS control room and archived for offline analysis



Monitoring locations

- 14 monitors in the Inner Detector

Module Panel Scale Help

en_US.iso88591

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Back root

RADMON

Sensors	READY	OK
RMSB 1 (IDEP)	OPERATIONAL	OK
RMSB 2 (IDEP)	OPERATIONAL	OK
RMSB 3 (IDEP)	OPERATIONAL	OK
RMSB 4 (IDEP)	OPERATIONAL	OK
RMSB 5 (Cryo)	OPERATIONAL	OK
RMSB 6 (PST)	OPERATIONAL	OK
RMSB 7 (IDEP)	OPERATIONAL	OK
RMSB 8 (IDEP)	OPERATIONAL	OK
RMSB 9 (PST)	OPERATIONAL	OK
RMSB 10 (Cryo)	OPERATIONAL	OK
RMSB 11 (IDEP)	OPERATIONAL	OK
RMSB 12 (IDEP)	OPERATIONAL	OK
RMSB 13 (PST)	OPERATIONAL	OK
RMSB 14 (PST)	OPERATIONAL	OK

3D View All connected

RMSB 3 (IDEP)

Sensor Information

Alias
IDE/RADMON/IDEP/Zp345/R80/Phi195 z=+345cm, r=80cm, phi=195

T 20.13 °C	RadFET 1 2.45e-9 Gy	DMILL 1 ~2.19e+9 n/cm2
PIN 1 6.36e+9 n/cm2	RadFET 2 0.00e+0 Gy	DMILL 2 ~5.22e+10 n/cm2
PIN 2 ~7.46e+9 n/cm2	RadFET 3 1.08e-1 Gy	EPI 2.00e+7 n/cm2

NB: - RF values: Total Ionising Dose (TID)

RADIATION MONITORING - Inner Detector

Temperature (RMSB) graph showing data for IDE:CAN5/RMSB1.

Monitoring locations and their values:

- IDE:CAN5/RMSB1: TID 0.00 Gy, TN -1e+011 n/cm2, EPI 4e+007 n/cm2, PIN 2e+010 n/cm2
- IDE:CAN8/RMSB0: TID 0.00 Gy, TN -1e+011 n/cm2, EPI 2e+007 n/cm2, PIN 5e+009 n/cm2
- IDE:CAN7/RMSB0: TID 0.00 Gy, TN -3e+009 n/cm2, EPI 2e+007 n/cm2, PIN 8e+009 n/cm2
- IDE:CAN7/RMSB1: TID 0.00 Gy, TN -5e+010 n/cm2, EPI 4e+007 n/cm2, PIN 8e+009 n/cm2
- IDE:CAN4/RMSB0: TID 0.00 Gy, TN 4e+010 n/cm2, EPI 1e+011 n/cm2, PIN 5e+010 n/cm2
- IDE:CAN4/RMSB1: TID 0.00 Gy, TN 3e+009 n/cm2, EPI 1e+011 n/cm2, PIN -8e+009 n/cm2
- IDE:CAN5/RMSB0: TID 0.00 Gy, TN 1e+011 n/cm2, EPI 4e+007 n/cm2, PIN 1e+011 n/cm2
- IDE:CAN8/RMSB1: TID 0.01 Gy, TN 2e+011 n/cm2, EPI 4e+011 n/cm2, PIN 2e+010 n/cm2
- IDE:CAN2/RMSB1: TID 0.00 Gy, TN -1e+011 n/cm2, EPI 4e+007 n/cm2, PIN 6e+009 n/cm2
- IDE:CAN2/RMSB0: TID 0.00 Gy, TN -2e+009 n/cm2, EPI 2e+007 n/cm2, PIN 6e+009 n/cm2
- IDE:CAN3/RMSB1: TID 0.00 Gy, TN -1e+011 n/cm2, EPI 4e+007 n/cm2, PIN 6e+009 n/cm2
- IDE:CAN3/RMSB0: TID 0.00 Gy, TN -2e+009 n/cm2, EPI 2e+007 n/cm2, PIN 6e+009 n/cm2
- IDE:CAN5/RMSB0: TID 0.00 Gy, TN 3e+010 n/cm2, EPI 4e+011 n/cm2, PIN 7e+010 n/cm2

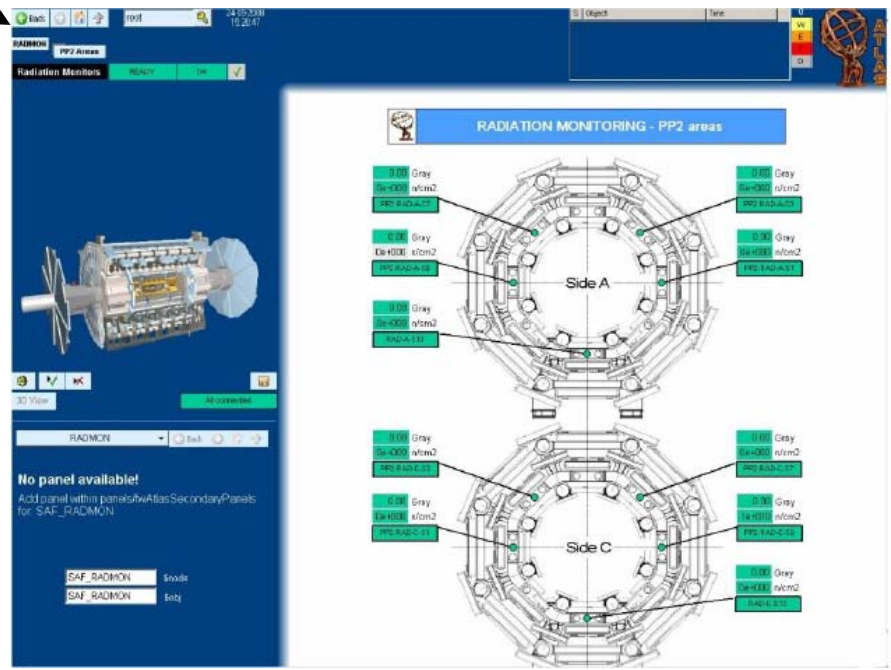
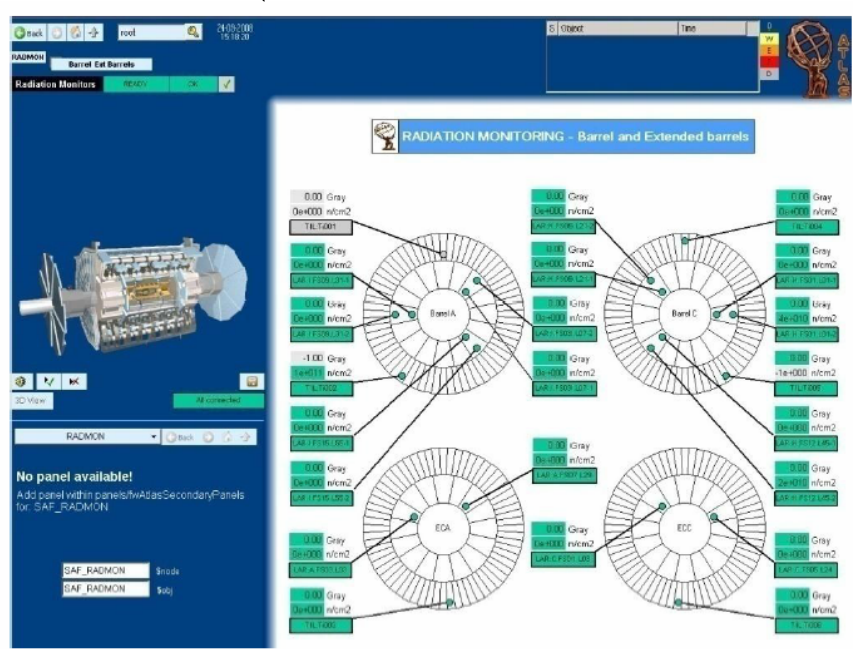
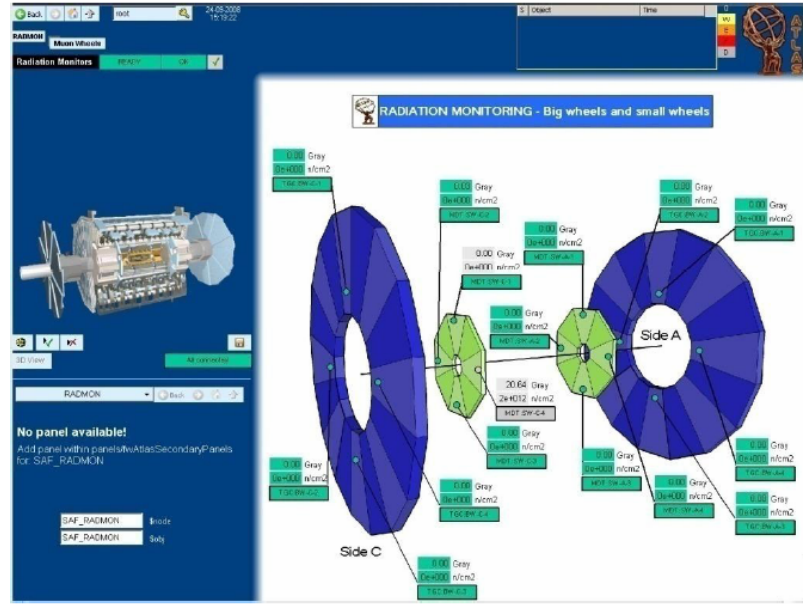
Monitoring locations

- 48 locations outside of the Inner Detector

Muon detectors

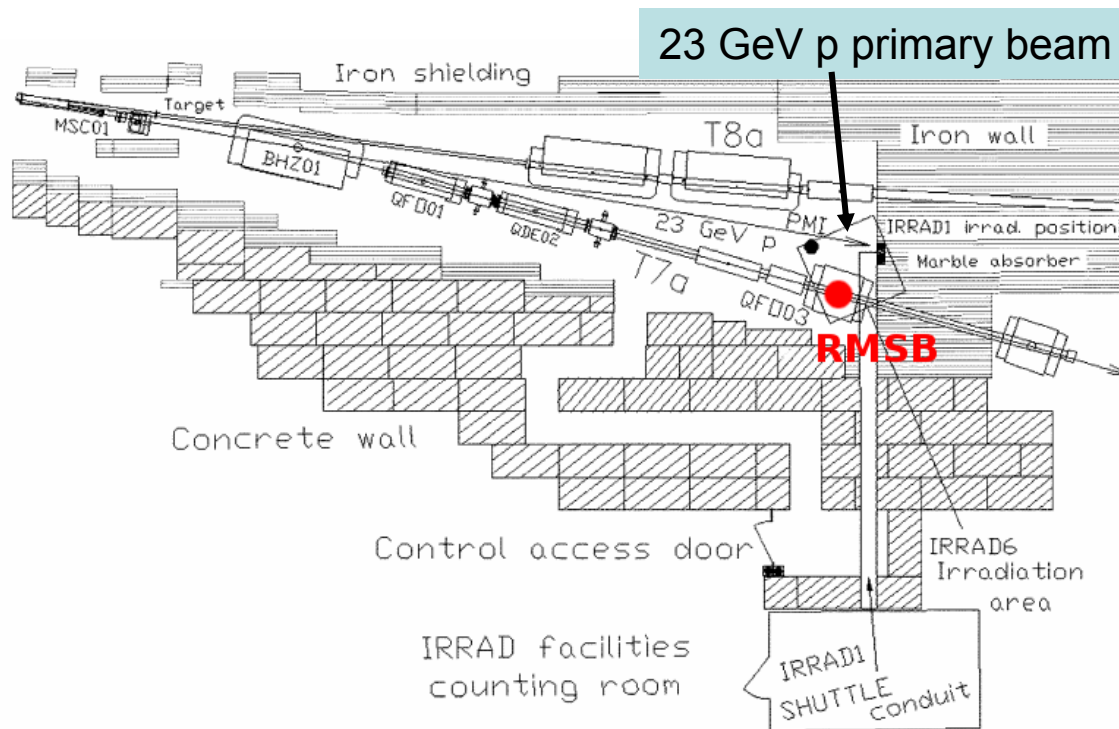
Calorimeters

TRT electronics



Tests in Mixed Radiation Environment

- 2 ID-type RMSBs with readout installed in the IRRAD6 irradiation facility at CERN in 2008
- mixture of pions, protons, neutrons, photons
- low dose rates, beam on-off
 - ➔ similar conditions as in ATLAS
- SEC counter Secondary Emission Counter (SEC): counts number of protons in primary beam
 - ➔ this number is proportional to the dose at RMSB location



F. Ravotti, M. Glaser et al., *IEEE TNS Vol. 54 (4)*, pp. 1170-1177, 2007.

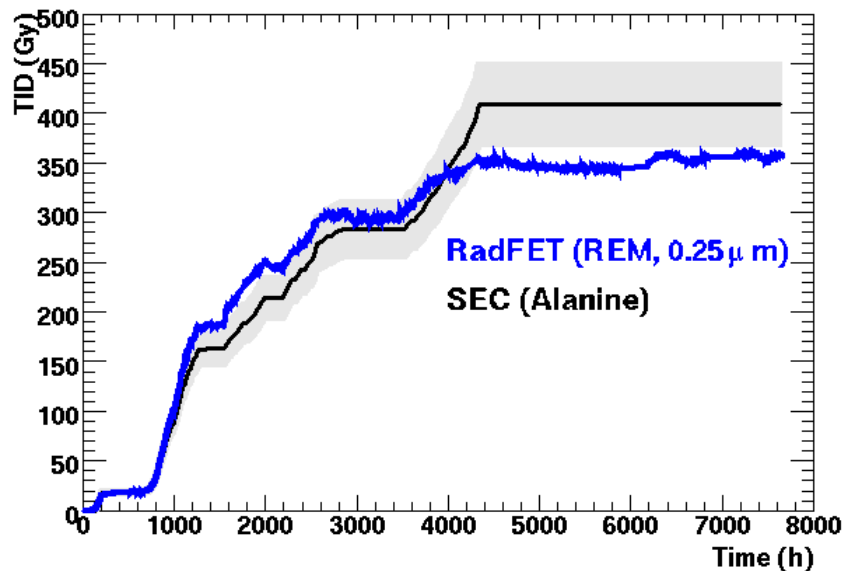
Tests in Mixed Radiation Environment

TID

- SEC counts converted to dose (Gy) with alanine dosimeter
 - dose 410 ± 20 Gy measured with alanine at the end of beam period (at 4000 h)

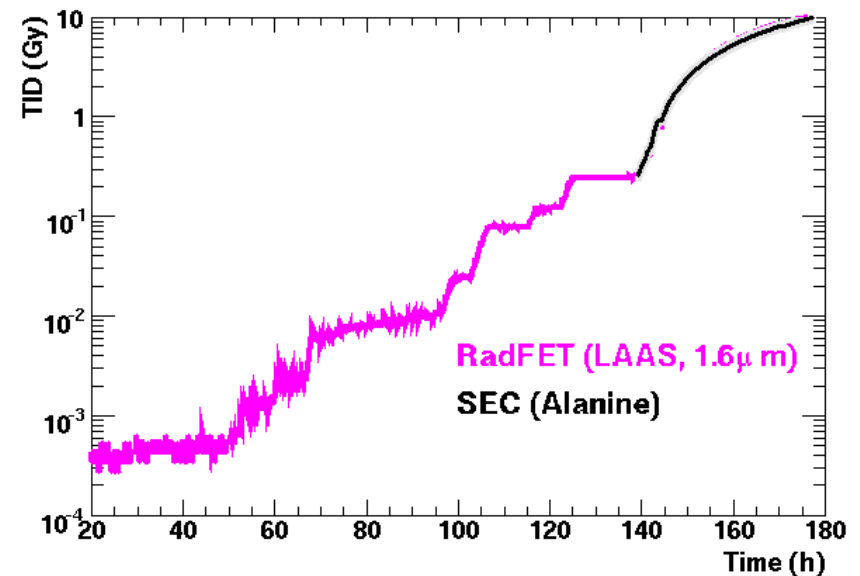
Medium Sensitivity

- good agreement with SEC
- no significant annealing



High Sensitivity RadFET

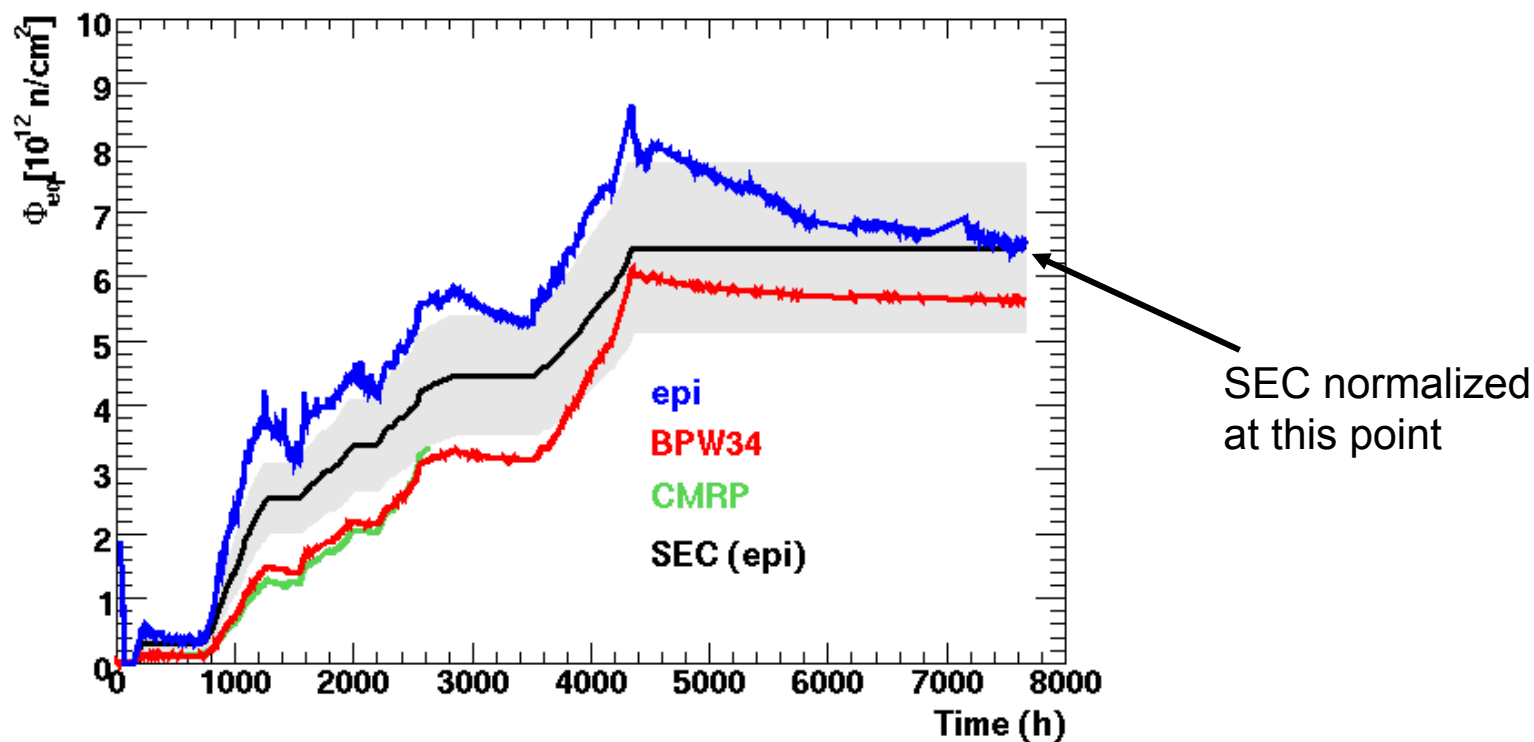
- mGy sensitivity



Tests in Mixed Radiation Environment

NIEL

- SEC counts converted to 1 MeV equivalent neutron fluence with epitaxial diode on RMSB
 - current $I = 0.11 \mu\text{A}$ measured at **Time ~ 8000 h**
 - with $\alpha = 2.7 \cdot 10^{-17} \text{ Acm}$ we get fluence $\Phi_{\text{eq}} = 6.5 \cdot 10^{12} \text{ n/cm}^2$



- raw measurements (no corrections for annealing)

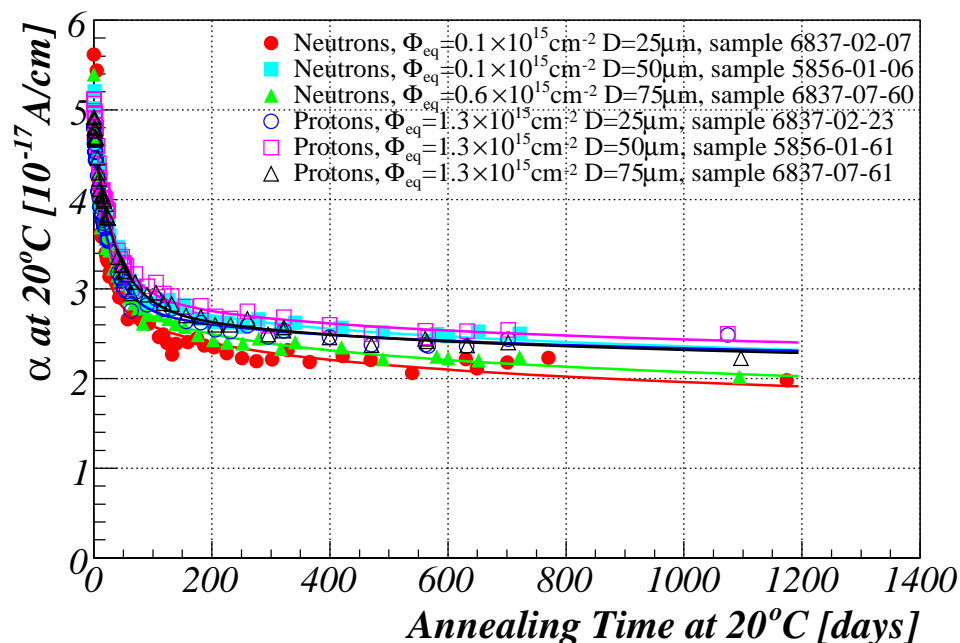
Annealing:

- approximation:

$$I(t) = I_1(t) + I_0$$

$$I_1(t) = V\Phi\alpha_1 \cdot e^{-\frac{t}{\tau}}; \quad I_0 = V\Phi\alpha_0$$

$$dI(t) = -\frac{I_1(t)}{\tau} dt$$



- change of current ΔI measured at time t in IRRAD6 after time interval Δt :

$$\Delta I = \alpha V \Delta \Phi - \frac{dI(t)}{dt} \cdot \Delta t$$

$$\Delta I = \alpha V \Delta \Phi - \frac{I_1(t)}{\tau} \cdot \Delta t$$

$$I_1(t) = I(t) - V\alpha_0\Phi(t)$$

$$\alpha = \alpha_1 + \alpha_0$$

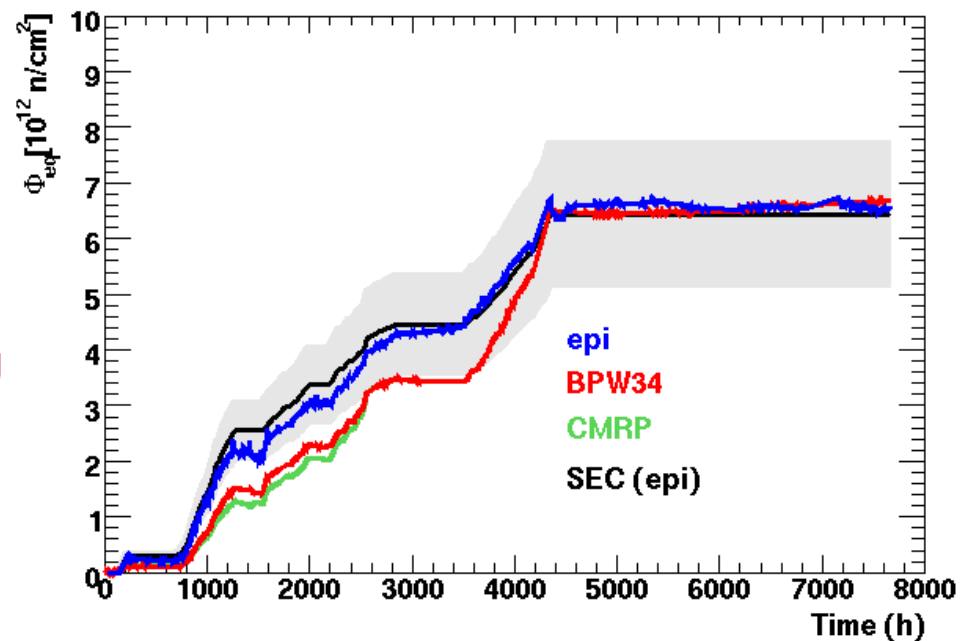
$$\Delta \Phi = \frac{1}{\alpha V} \left(\Delta I + \frac{I_1(t)}{\tau} \cdot \Delta t \right)$$

Tests in Mixed Radiation Environment

NIEL

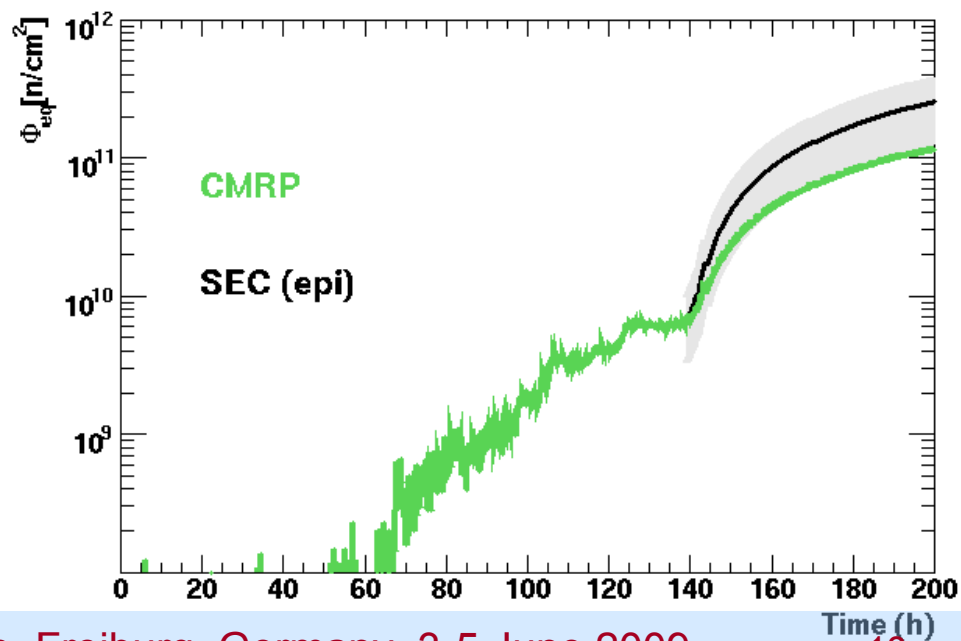
All diodes:

- epi → reverse bias
- BPW34 → forward bias
- CMRP → forward bias
- epi and BPW34 corrected for annealing



High Sensitivity PiN diode (CMRP)

- measure forward bias @ $I = 1 \text{ mA}$
- sensitivity $\sim 10^9 \text{ n/cm}^2$



Tests in Mixed Radiation Environment

Thermal neutrons

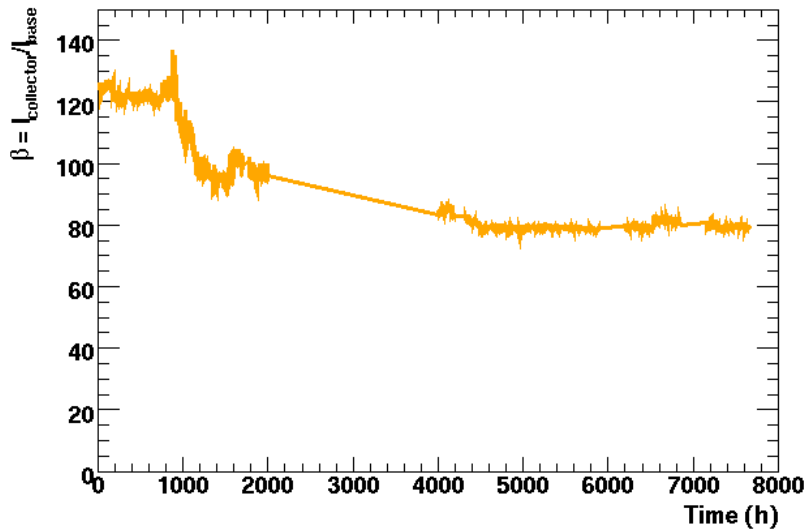
- base current I_b measured at collector current $I_c = 10 \mu\text{A}$

1. monitor current gain $\beta = I_c/I_b$

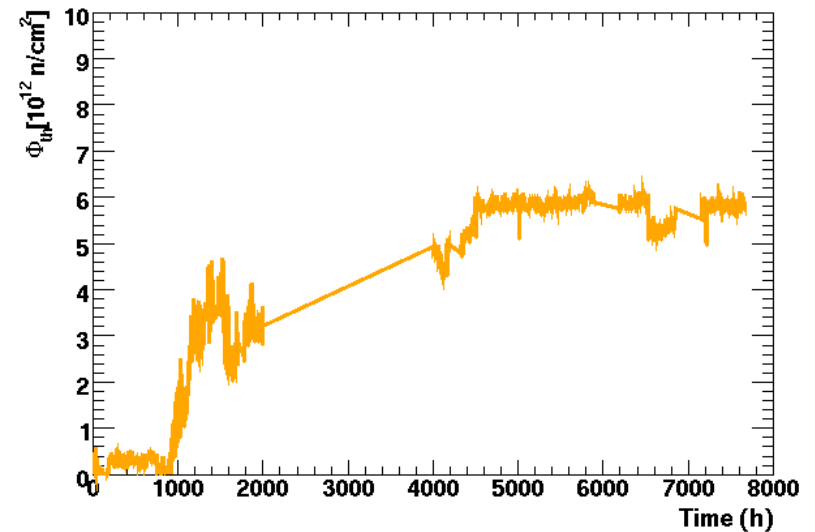
2. measure fluence of thermal neutrons:

$$\rightarrow \Phi_{\text{th}} = 1/k_{\text{th}} (DI_b/I_c - k_{\text{eq}} \cdot \Phi_{\text{eq}}), \quad \Phi_{\text{eq}}: \text{measured with BPW34}$$

β degradation



Thermal neutron fluence



Experience from ATLAS

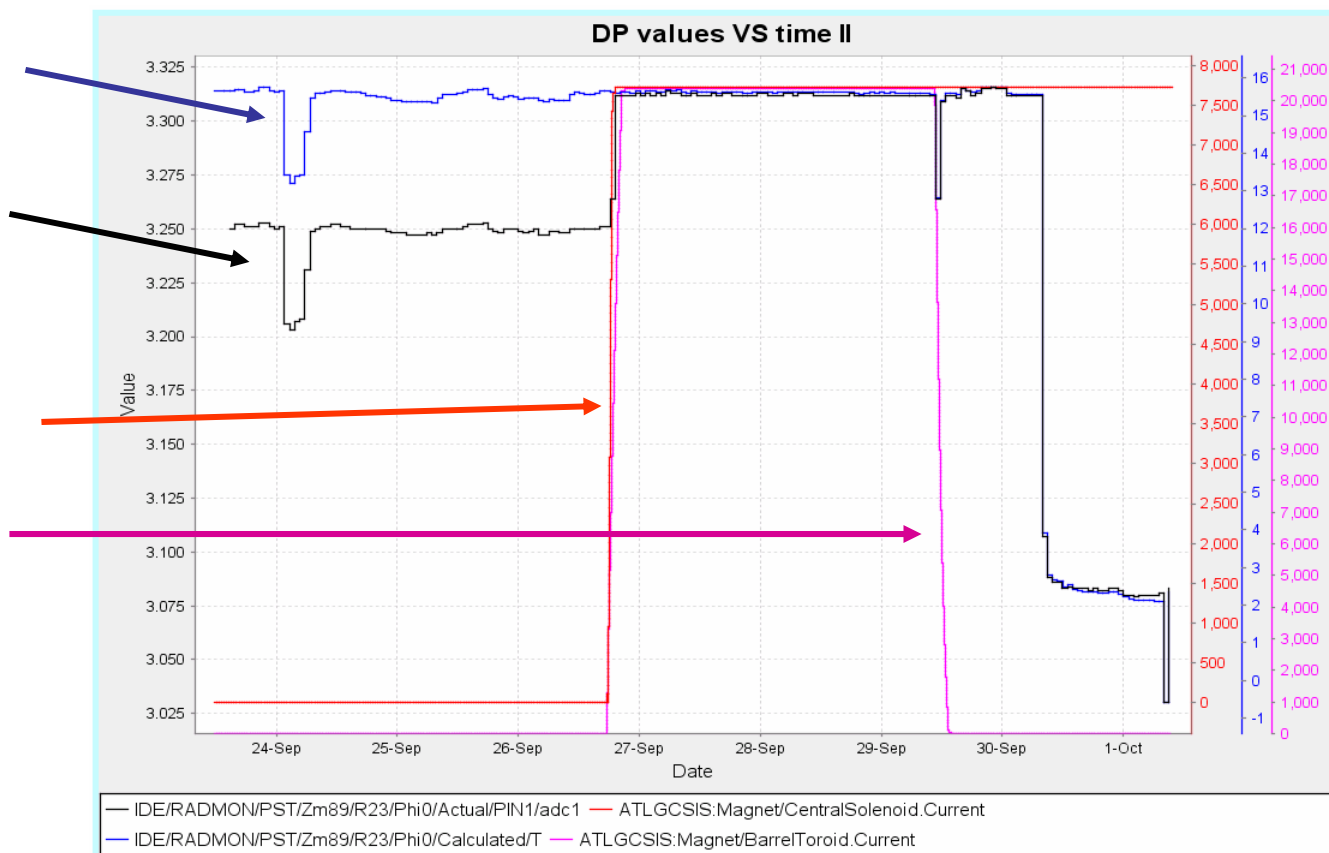
- complete system was installed and integrated in ATLAS DCS in 2008
- stability checked, temperature dependences measured
 - ➔ surprise: response of diodes operated in forward bias influenced by magnetic field

Temperature

Diode Voltage

Solenoid field

Toroid field



- later tests showed that the effect doesn't change with fluence ➔ can be subtracted

- system for online radiation monitoring in ATLAS Inner Detector:
 - total ionization dose in SiO_2
 - bulk damage in silicon in terms of 1 MeV equivalent neutron fluence
 - fluence of thermal neutrons (Inner Detector only)
 - readout compatible with ATLAS Detector Control System
- tests in mixed radiation environment
 - sufficient sensitivity: $\text{TID} \sim \text{mGy}$, $\Phi_{\text{eq}} \sim 10^9 \text{ n/cm}^2$
 - sufficient accuracy: $\sim 20\%$
 - annealing effect can be controlled

- complete system was installed and integrated in ATLAS DCS in 2008
 - few months of data taking in 2008
 - good stability

Ready to measure doses!

